



STD15NF10

N-channel 100 V, 0.060 Ω , 23 A, DPAK
low gate charge STripFET™ II Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} max	I _D
STD15NF10	100 V	< 0.065 Ω	23 A

- Exceptional dv/dt capability
- 100% avalanche tested
- Application oriented characterization

Application

- Switching applications

Description

This MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for telecom and computer applications. It is also intended for any applications with low gate drive requirements.

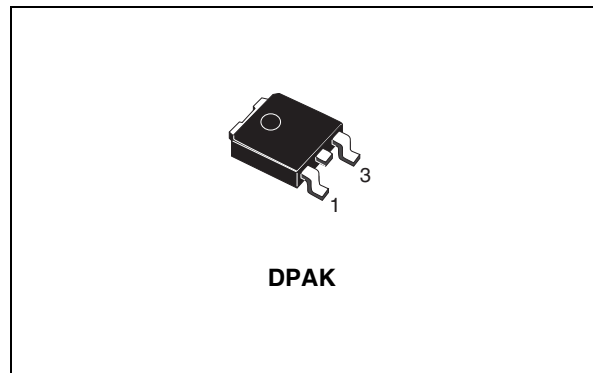


Figure 1. Internal schematic diagram

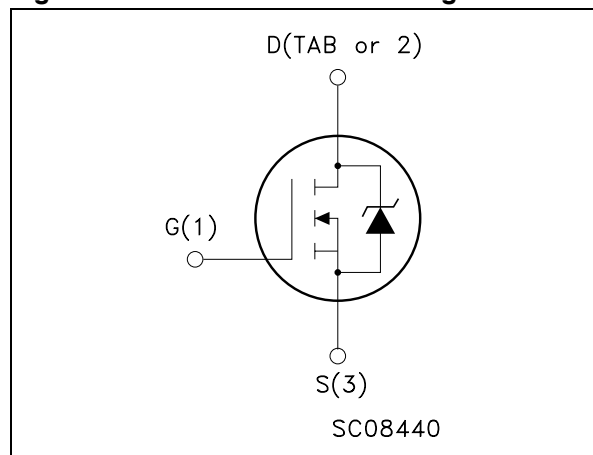


Table 1. Device summary

Order code	Marking	Package	Packaging
STD15NF10T4	D15NF10	DPAK	Tape and reel

Contents

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	100	V
V_{DGR}	Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)	100	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25 \text{ }^\circ\text{C}$	23	A
I_D	Drain current (continuous) at $T_C = 100 \text{ }^\circ\text{C}$	16	A
$I_{DM}^{(1)}$	Drain current (pulsed)	92	A
P_{TOT}	Total dissipation at $T_C = 25 \text{ }^\circ\text{C}$	70	W
	Derating factor	0.46	W/ $^\circ\text{C}$
$E_{AS}^{(2)}$	Single pulse avalanche energy	180	mJ
$dv/dt^{(3)}$	Peak diode recovery voltage slope	9	V/ns
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_J	Max. operating junction temperature		

1. Pulse width limited by safe operating area
2. Starting $T_J = 25 \text{ }^\circ\text{C}$, $I_D = 10\text{A}$, $V_{DD} = 30\text{V}$
3. $I_{SD} \leq 13 \text{ A}$, $di/dt \leq 300 \text{ A}/\mu\text{s}$, $V_{DS} \leq V_{(BR)DSS}$, $T_J \leq T_{JMAX}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case max	2.14	$^\circ\text{C}/\text{W}$
R_{thJA}	Thermal resistance junction-ambient max	100	$^\circ\text{C}/\text{W}$
T_I	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On⁽¹⁾ /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	100			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating, @ } 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\ \text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\ \text{V}$, $I_D = 12\ \text{A}$		0.06	0.065	Ω

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\ \text{V}$, $I_D = 7.5\ \text{A}$		12		S
C_{iss}	Input capacitance	$V_{DS} = 25\ \text{V}$, $f = 1\ \text{MHz}$, $V_{GS} = 0$		870		pF
C_{oss}	Output capacitance			125		pF
C_{rss}	Reverse transfer capacitance			50		pF
Q_g	Total gate charge	$V_{DD} = 80\ \text{V}$, $I_D = 24\ \text{A}$ $V_{GS} = 10\ \text{V}$		30	40	nC
Q_{gs}	Gate-source charge			6		nC
Q_{gd}	Gate-drain charge			10		nC

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 50\ \text{V}$, $I_D = 12\ \text{A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\ \text{V}$ <i>Figure 13 on page 8</i>		60		ns
t_r	Rise time			45		ns
$t_{d(off)}$	Turn-off delay time			49		ns
t_f	Fall time			17		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				23	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				92	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 20 \text{ A}$, $V_{GS} = 0$			1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 24 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 30 \text{ V}$, $T_J = 150 \text{ }^\circ\text{C}$ <i>Figure 15 on page 8</i>		100		ns
Q_{rr}	Reverse recovery charge			375		nC
I_{RRM}	Reverse recovery current			7.5		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

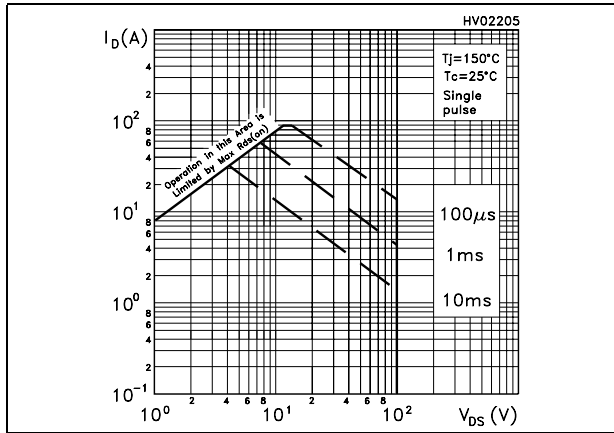


Figure 3. Thermal impedance

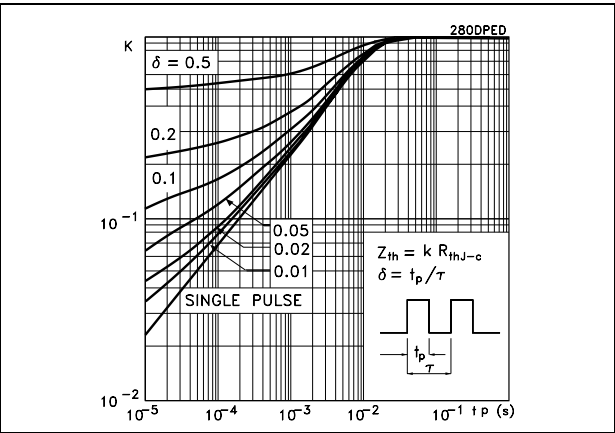


Figure 4. Output characteristics

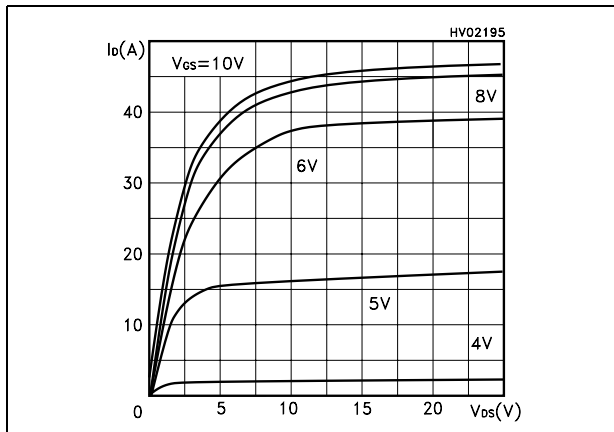


Figure 5. Transfer characteristics

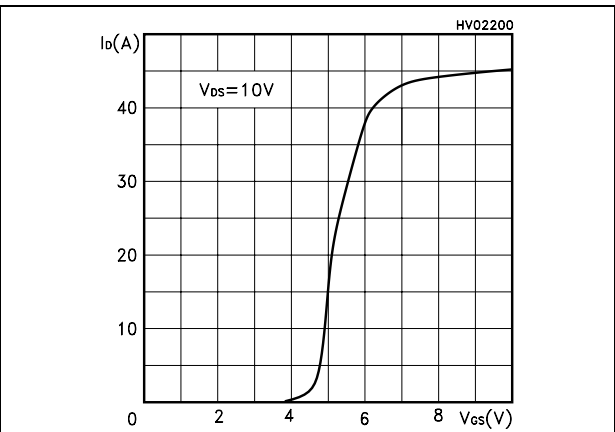


Figure 6. Transconductance

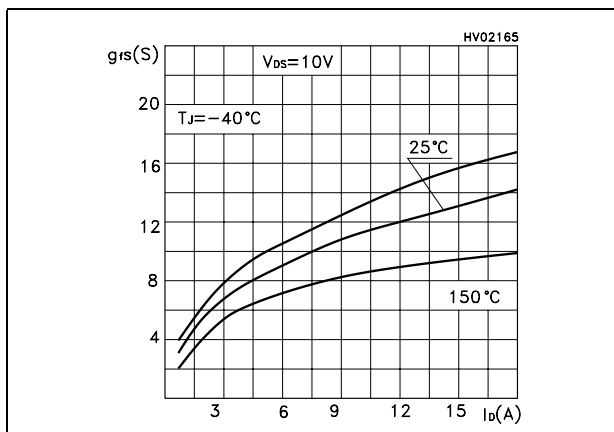


Figure 7. Static drain-source on resistance

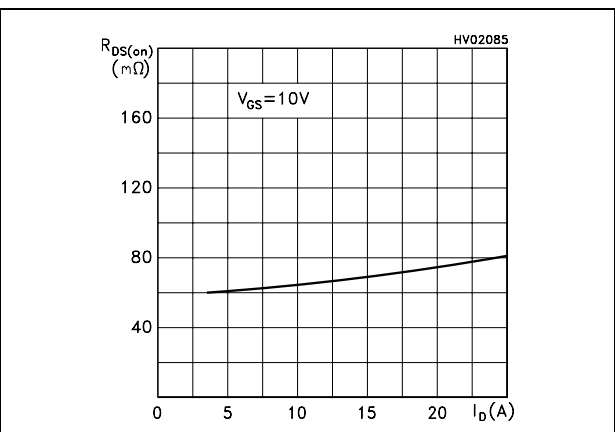


Figure 8. Gate charge vs. gate-source voltage Figure 9. Capacitance variations

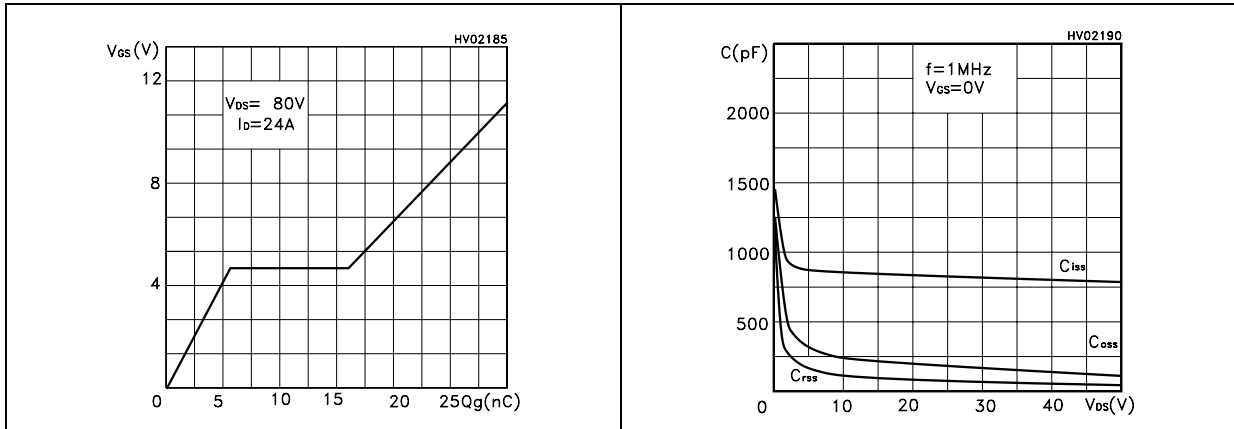


Figure 10. Normalized gate threshold voltage vs. temperature Figure 11. Normalized on resistance vs. temperature

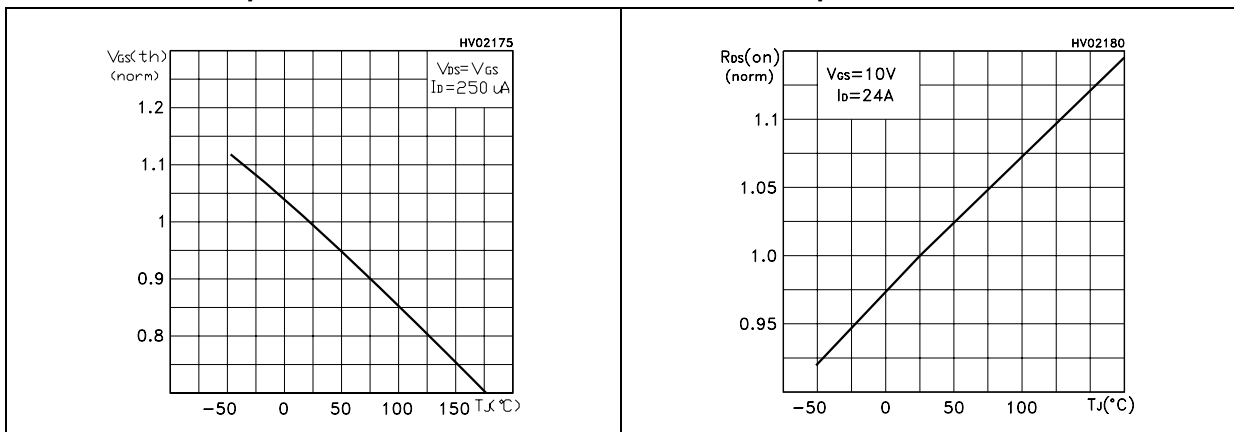
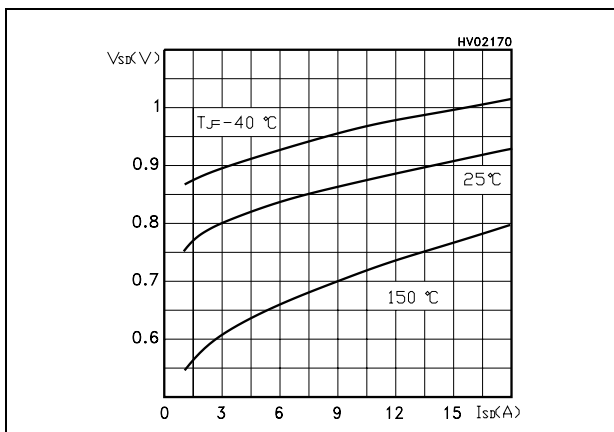


Figure 12. Source-drain diode forward characteristics



3 Test circuit

Figure 13. Switching times test circuit for resistive load

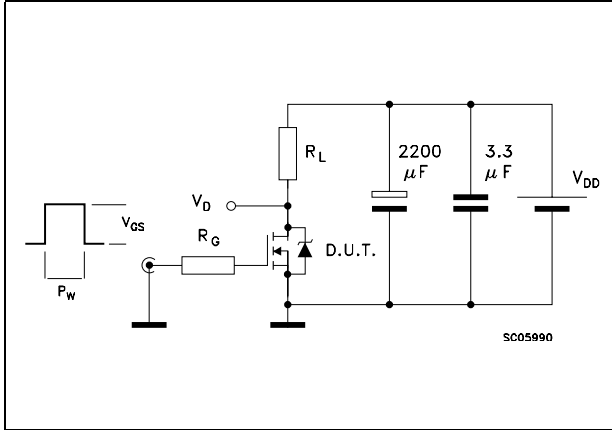


Figure 14. Gate charge test circuit

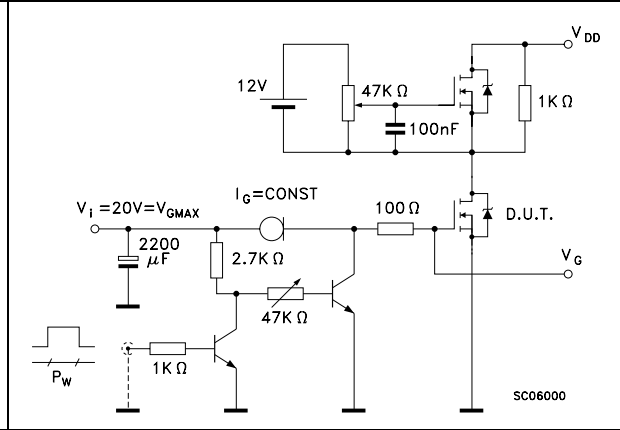


Figure 15. Test circuit for inductive load switching and diode recovery times

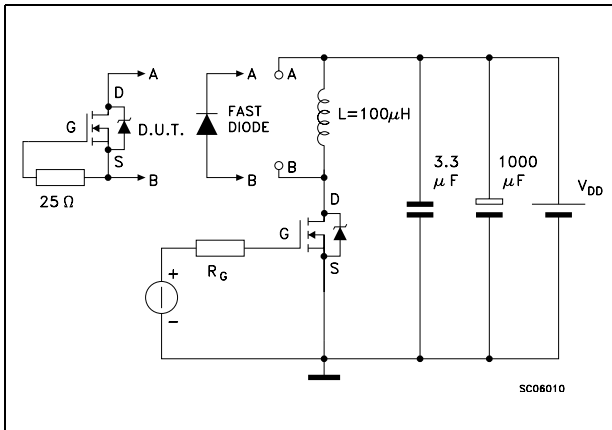


Figure 16. Unclamped Inductive load test circuit

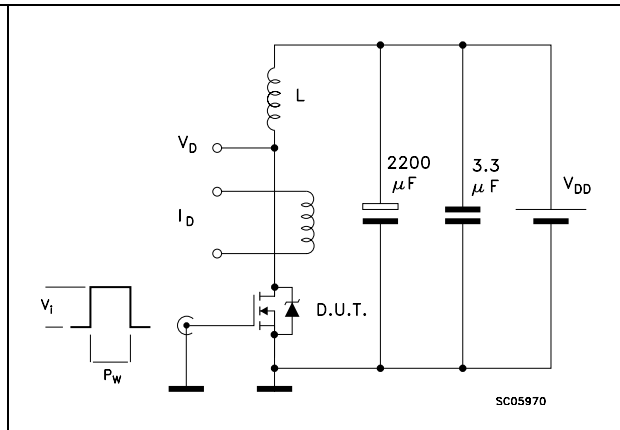
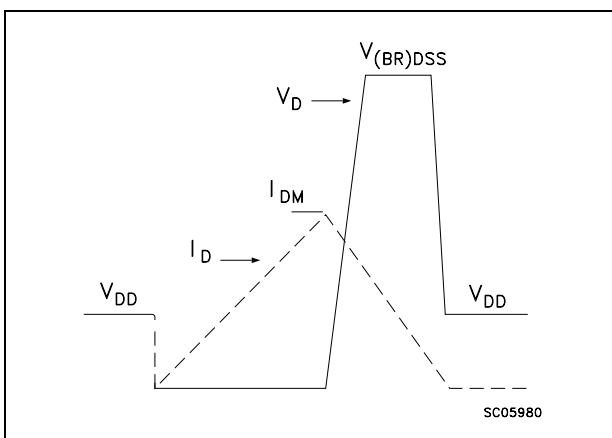


Figure 17. Unclamped inductive waveform

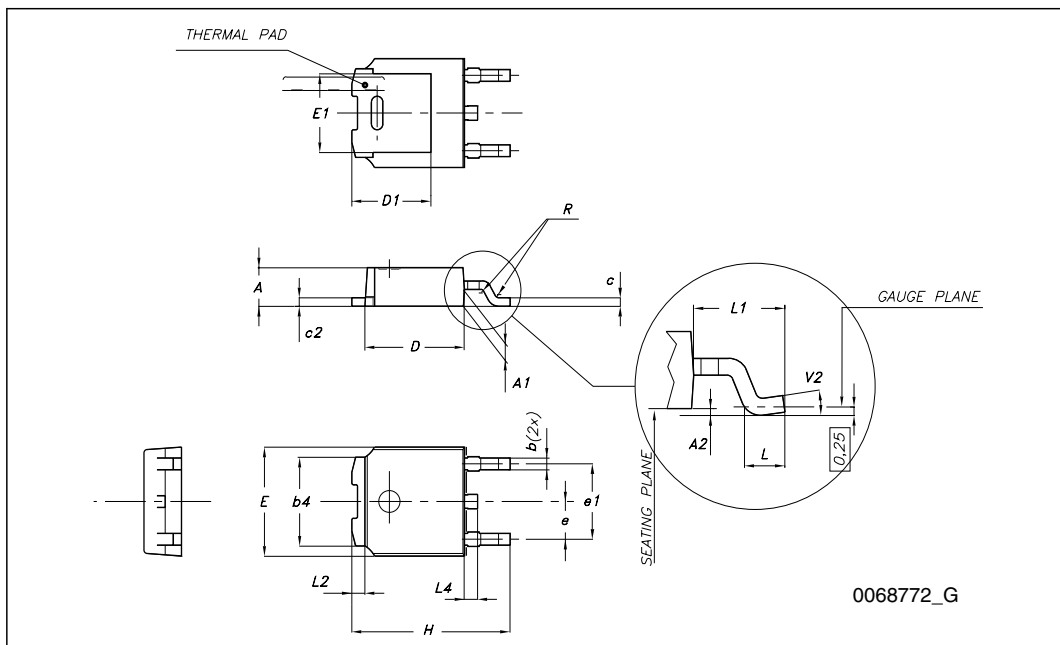


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

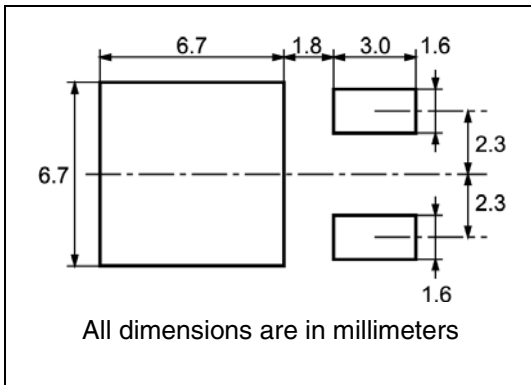
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY		BULK QTY	
2500		2500	

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

TOP COVER TAPE

10 pitches cumulative tolerance on tape +/- 0.2 mm

User Direction of Feed

Center line of cavity

TRL

FEED DIRECTION

Bending radius R min.

For machine ref. only including draft and radii concentric around B0

6 Revision history

Table 8. Revision history

Date	Revision	Changes
21-Jun-2004	3	No history because migration.
09-Sep-2004	4	Complete document
08-Aug-2006	5	New template, updated SOA
04-Nov-2008	6	Q _G max value in Table 5 has been corrected.

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